

GS431

Adjustable Precision Shunt Regulators

Product Description

The GS431 is a three-terminal adjustable shunt regulator with specified thermal stability.

The output voltage may be set to any value between V_{REF} and 36V with two external resistors.

This device has a typical output impedance of 0.2Ω. Active output circuitry provides very sharp turn-on characteristics, making this device excellent replacement for Zener diodes in many applications.

GS431 is available in SOT-23 package.

Features

- Temperature-Compensated for Operation over Full Rated Operating Temperature Range.
- Adjustable Output Voltage
- Low (0.2Ω Typ.) Dynamic Output Impedance
- Low Output Noise
- Fast Turn-on Response
- RoHS Compliant & Halogen Free

Applications

- Battery Operated Computer
- Switching Power Supplies
- Adjustable Power Supplies
- Linear Regulators
- Instrumentation
- Computer Disk Drivers

Typical Application

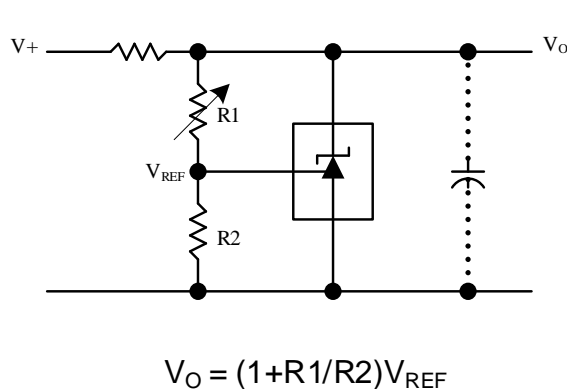


Figure 1. Shunt Regulator

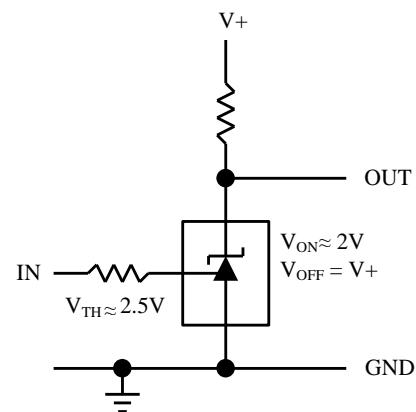
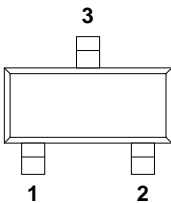
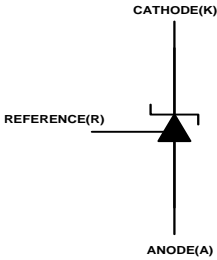


Figure 2. Single Supply Comparator with Temperature Compensated Threshold

Packages & Pin Assignments

SOT-23		Equivalent Circuit	
			
GS431JZF		GS431JWF	
Pin	Function	Pin	Function
1	REF	1	CATHODE
2	CATHODE	2	REF
3	ANODE	3	ANODE

Ordering and Marking Information

Ordering Information		
Device	Package	Quantity/Reel
GS431JZF	SOT-23	3000PCS
GS431JWF	SOT-23	3000PCS
GS431 1 1 F Product Code: GS431		
Package Code: 1 1 is JZ and JW <ul style="list-style-type: none"> - Both are SOT-23 - Pin Assignment please refer to Pin Assignments section 		
Green Level: F stands for RoHS Compliant and Halogen Free		
Marking Information		
4 1 2 2 2 2 Product Code: - 4		
Pin Assignment: 1 is C or D <ul style="list-style-type: none"> - C for GS431JWF - D for GS431JZF 		
GS Code: 2 2 2 2 is GS Code		

Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{KA}	Cathode Voltage (Note 1)	37	V
I_K	Continuous Cathode Current Range	-10 to +150	mA
I_{REF}	Reference Current Range	-50 μ A to 10mA	mA
P_D	Power Dissipation	0.23	W
T_{OPR}	Operating Temperature Range	-40 to 125	$^{\circ}$ C
T_J	Junction Temperature	+150	$^{\circ}$ C
T_{STG}	Storage Temperature Range	-65 to 150	$^{\circ}$ C
T_{LEAD}	Lead Temperature Range(Soldering, 10sec)	260	$^{\circ}$ C

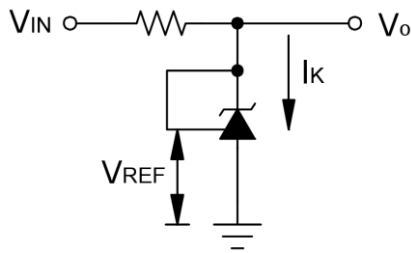
Note 1: Voltage values are with respect to the anode terminal unless otherwise noted.

Electrical Characteristics

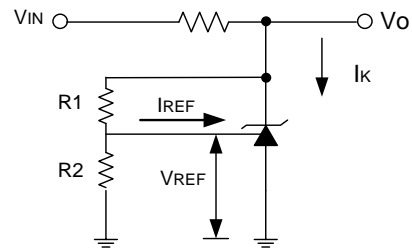
Electrical Characteristics at 25 $^{\circ}$ C free-air temperature (unless otherwise noted).

Symbol	Parameter	Conditions	GS431			Units
			Min	Typ	Max	
V_{REF}	Reference Voltage	$V_{KA}=V_{REF}$, $I_K=10mA$	2.483	2.495	2.507	V
V_{DEV}	Deviation of reference input voltage over full temperature range	$V_{KA}=V_{REF}$, $I_K=10mA$, T_A = Full range (Test circuit 1)		6.0	16	mV
$\frac{\Delta V_{REF}}{\Delta V_{KA}}$	Ratio of change in reference input voltage to the change in cathode voltage	$I_K=10mA$, $\Delta V_{KA}=10V$ to V_{REF} $\Delta V_{KA}=36V$ to $10V$	-2.7 -2	-1.4 -1		mV/V
I_{REF}	Reference input current	$I_K=10mA$, $R1=10K\Omega$, $R2=\infty$ (Test circuit 2)		1	4.0	μ A
I_{REF} (DEV)	Deviation of reference input current over full temperature range	$I_K=10mA$, $R1=10K\Omega$, $R2=\infty$, T_A = Full range (Test circuit 2)		0.4	1.2	μ A
I_K (min)	Minimum cathode current for regulation	$V_{KA} = V_{REF}$ (Test circuit 1)		0.4	1.0	mA
I_K (off)	Off-state cathode current	$V_{KA}=36V$, $V_{REF}=0$ (Test circuit 3)		0.1	1.0	μ A
$ Z_{KA} $	Dynamic impedance	$f < 1KHz$, $V_{KA} = V_{REF}$ $I_K=1mA$ to $100mA$		0.2	0.5	Ω

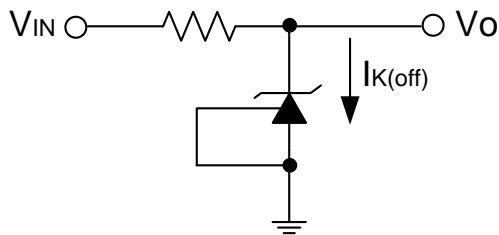
Test Circuits



Test Circuit 1.
 $V_{KA} = V_{REF}$

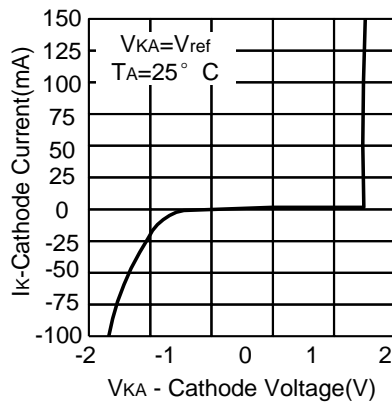


Test Circuit 2.
 $V_{KA} > V_{REF}$

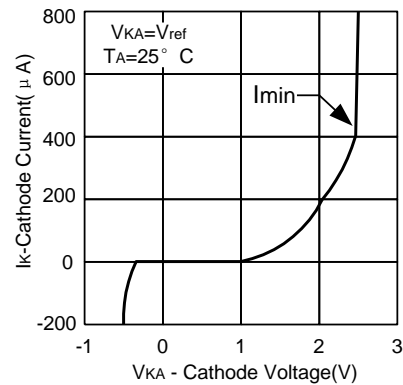


Test Circuit 3.
Off-State Current

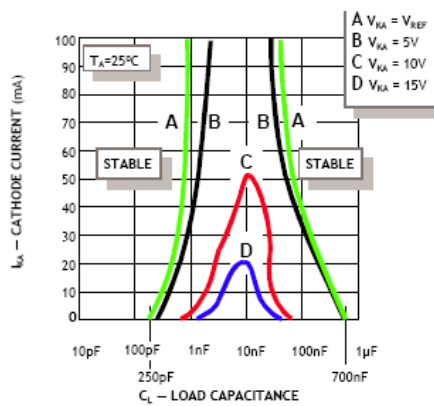
Typical Performance Characteristics



Cathode current vs. cathode voltage



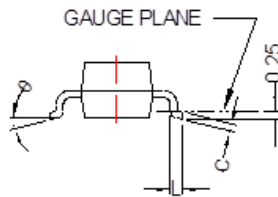
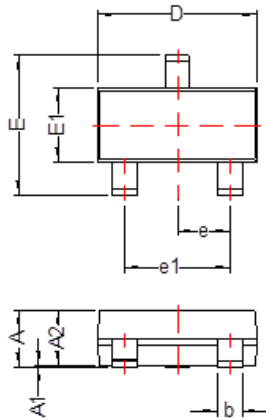
Cathode current vs. cathode voltage



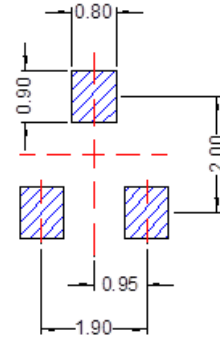
Stability Boundary Conditions

SOT-23

Package Dimension



Recommended Land Pattern



Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.75	1.17	0.030	0.046
A1	0.01	0.15	0.000	0.006
A2	0.70	1.02	0.028	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.3	0.6	0.012	0.024
θ	0°	8°	0°	8°





NOTE:



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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